



Form PTO 1449 (Rev. 2-32) U.S. Department of Commerce Patent and Trademark Office					Atty. Docket No. ACT-376	Serial No. 10/625,491	
Information Disclosure Statement by Applicant					Applicant: Chen et al.		
(Use several sheets if necessary)					Filed: July 22, 2003	Group: 2815	
U.S. Patent Documents							
Init.		Document No.	Date	Name	Class	Subclass	Filing Date
1		6,154,410	11/28/2000	Cutter et al.	365	225.7	02/05/1997
2		6,259,130 B1	07/10/2001	Wu	257	314	03/09/1999
3		6,413,833 B2	07/02/2002	Yamamoto	438	398	01/29/1999
4		6,440,869 B1	08/27/2002	Tseng	438	734	06/26/2000
Foreign Documents							
Translation							
Init.		Document No.	Date	Country	Class	Subclass	Yes No
<i>[Handwritten notes and lines through the table rows]</i>							
Other Documents (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>Watanabe</i>	<i>2/28/04</i>	H. Watanabe et al., "An Advanced Technique for Fabricating Hemispherical-Grained (HSG) Silicon Storage Electrodes", <i>IEEE Transactions On Electron Devices</i> , Vol. 42, NO. 2, pp. 295-300, February 1995.					
<i>[Handwritten notes and lines through the table rows]</i>							
Examiner <i>Watanabe</i>					Date Considered <i>8/28/04</i>		
Examiner: Initial if citation considered, whether or not citation is in conference with MPEP 609; Draw line through citation if not conformance and not considered. Include a copy of this form with the next communication to applicant.							